

Technical Data Green Products

Data Sheet N1231, Rev. B

409CNQ135/409CNQ150 SCHOTTKY RECTIFIER

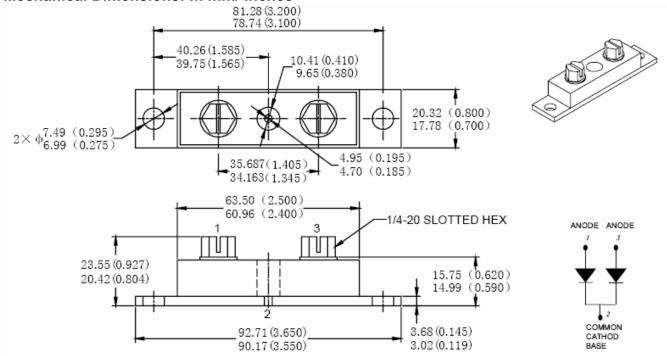
Applications:

- High current switching power supply Plating power supply Free-Wheeling diodes
- Reverse battery protection Converters UPS System Welding

Features:

- 175°C T_J operation
- Center tap module
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- · Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- · Additional testing can be offered upon request

Mechanical Dimensions: In mm/ Inches



PRM4 (Non-Isolated)

MARKING.MOLDING RESIN

Marking for 409CNQ135/150, 1st row SS YYWWL, 2nd row 409CNQ135/150 Where YY is the manufacture year WW is the manufacture week code L is the wafer's Lot Number Molding resin

Epoxy resin UL:94V-0

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Maximum Ratings:

Characteristics	Symbol	Condition	Max.		Units
Peak Inverse Voltage	V_{RWM}	-	135	409CNQ135	V
			150	409CNQ150	
Max. Average Forward	I _{F(AV)}	50% duty cycle @T _C =105°C,	200	per leg	Α
Current		rectangular wave form	400	per device	
Max. Peak One Cycle Non- Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	2760		А

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units	
Max. Forward Voltage Drop (per leg) *	V_{F1}	@ 200A, Pulse, T _J = 25 °C	1.03	\/	
		@ 400A, Pulse, T _J = 25 °C	1.21	V	
	V_{F2}	@ 200A, Pulse, T _J = 125 °C	0.72	\/	
		@ 400A, Pulse, T _J = 125 °C	0.83	V	
Max. Reverse Current (per	I_{R1}	$@V_R = \text{rated } V_R T_J = 25 ^{\circ}\text{C}$	6	mA	
leg) *	I_{R2}	$@V_R = \text{rated } V_R T_J = 125 ^{\circ}\text{C}$	85	mA	
Max. Junction Capacitance (per leg)	C _T	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	6000	pF	
Typical Series Inductance (per leg)	Ls	Measured lead to lead 5 mm from package body	5.0	nΗ	
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs	

^{*} Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specifi	Units			
Max. Junction Temperature	T _J	-	-55 to	°C			
Max. Storage Temperature	T _{stg}	-	-55 to	°C			
Maximum Thermal Resistance Junction to Case (per leg)	$R_{ heta JC}$	DC operation	0.20		°C/W		
Maximum Thermal Resistance Junction to Case (per package)	$R_{ heta JC}$	DC operation	0.10		°C/W		
Typical Thermal Resistance, case to Heat Sink	$R_{\theta cs}$	Mounting surface, smooth and greased	0.10		°C/W		
Mounting Torque	Тм	-	Mounting Torque Terminal Torque	24(min) 35(max) 35(min) 46(max)	Kg-cm		
Approximate Weight	wt	-	79		g		
Case Style	PRM4 Non-Isolated						

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Typical Forward Characteristics Typical Reverse Characteristics Instantaneous Reverse Current - IR (mA) 10¹ 150°C 10² 10⁰ 175 °C 10⁻¹ Instantaneous Forward Current - I_F (A) 125 °C 10¹ 75 10⁻² 10⁻³ 25 10⁻⁴ 10° 25% 0 20 80 100 120 140 Reverse Voltage - V_R (V) Typical Junction Capacitance 10⁻¹ 25 °C 10⁻² 1200 0.0 0.4 0.6 1.0 0 40 80 120 160 Forward Voltage Drop - VF (V) Reverse Voltage - V_R (V)

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